

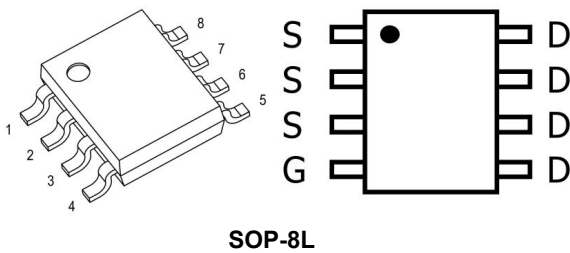
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	7.5mΩ@10V	10.3A
	9mΩ@4.5V	

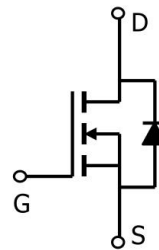
Feature

- $V_{DS} = 30V, I_D = 10.3A$
 $R_{DS(ON)} < 9m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS} = 4.5V$
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed

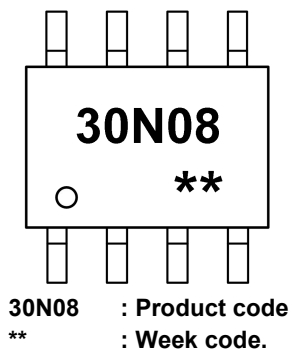
Package



Circuit diagram



Marking



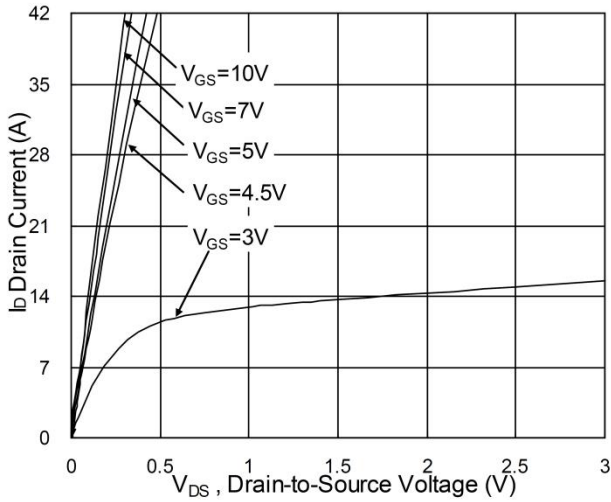
**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	10.3	A
Pulsed Drain Current	I_{DM}	42	A
Maximum Power Dissipation(Tc=25°C)	P_D	1.5	W
Thermal Resistance,Junction-to-Case	$R_{\theta Jc}$	85	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

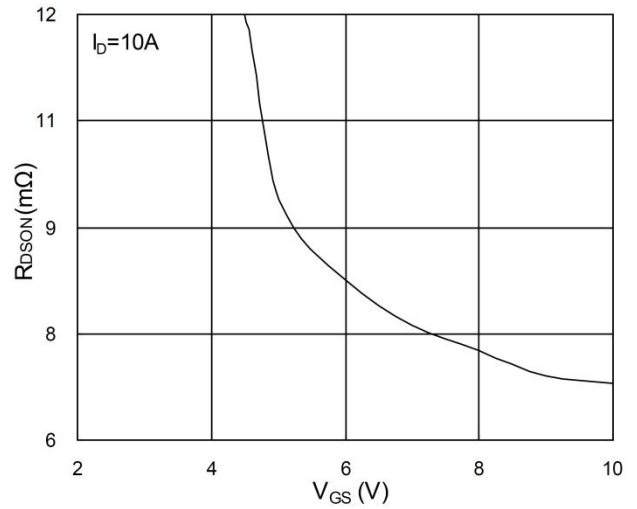
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$		7.5	9	mΩ
		$V_{GS}=4.5V, I_D=6A$		9	14	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, f=1.0MHz$		1317		pF
Output Capacitance	C_{oss}			163		pF
Reverse Transfer Capacitance	C_{rss}			131		pF
Switching Times						
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=15V, I_D=10A, R_{GEN}=3.3\Omega$		6.2		nS
Turn-on Rise Time	t_r			59		nS
Turn-Off Delay Time	$t_{d(off)}$			27.6		nS
Turn-Off Fall Time	t_f			8.4		nS
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=25V, I_D=12A$		12.6		nC
Gate-Source Charge	Q_{gs}			4.2		nC
Gate-Drain Charge	Q_{gd}			5.1		nC
Source-Drain Diode Characteristics						
Gate-Drain Charge	V_{SD}	$V_{GS}=0V, I_S=1A$			1.2	V

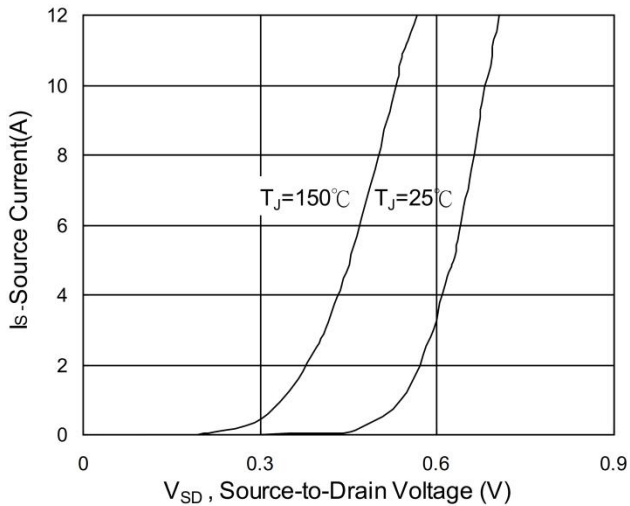
Typical Characteristics



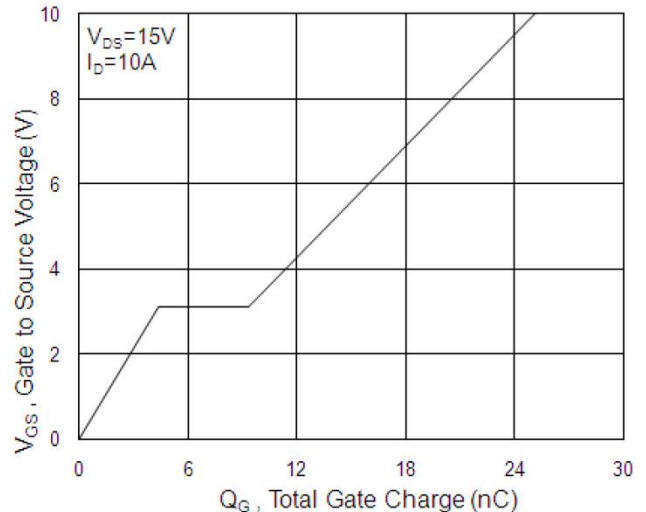
Typical Output Characteristics



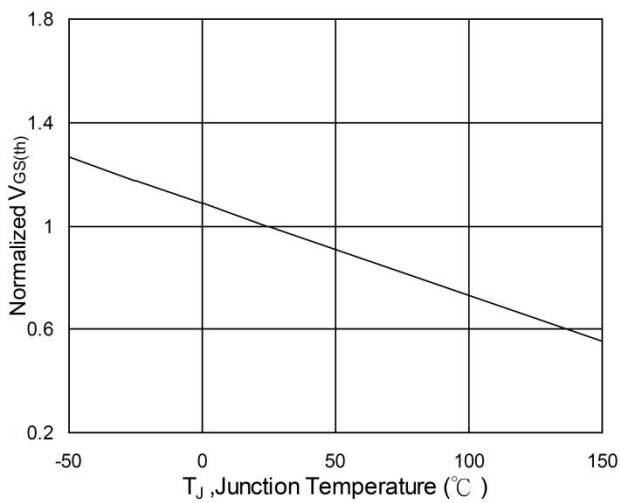
On-Resistance vs. Gate-Source



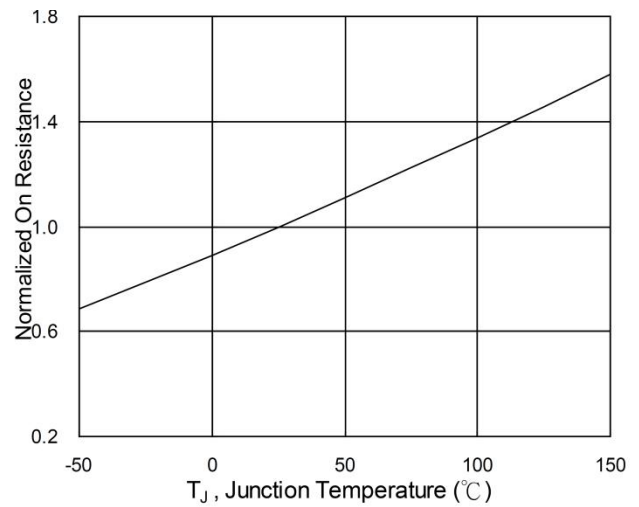
Forward Characteristics of reverse



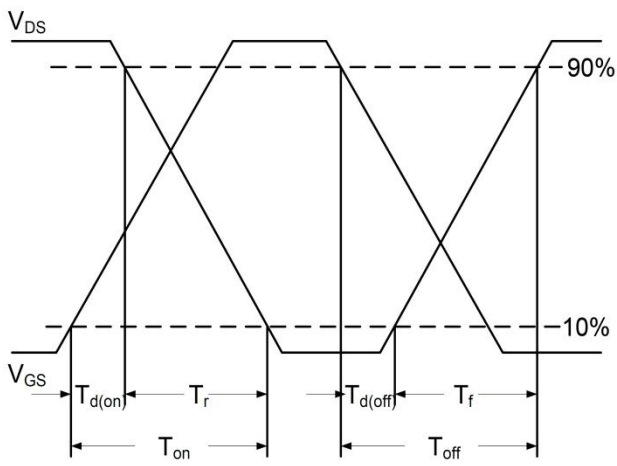
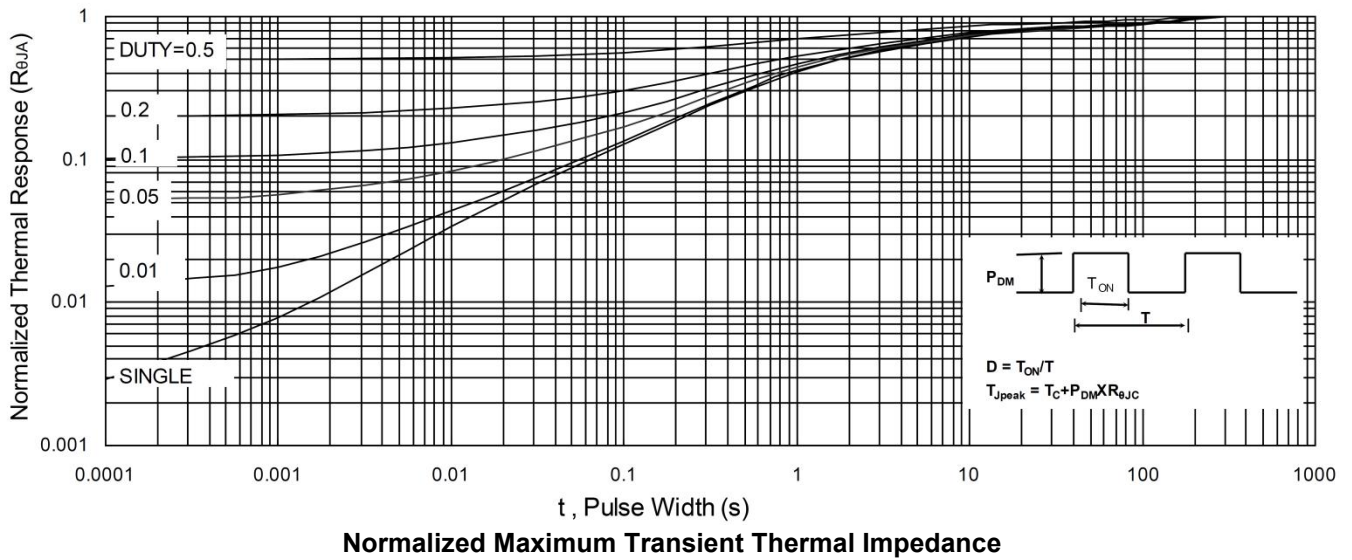
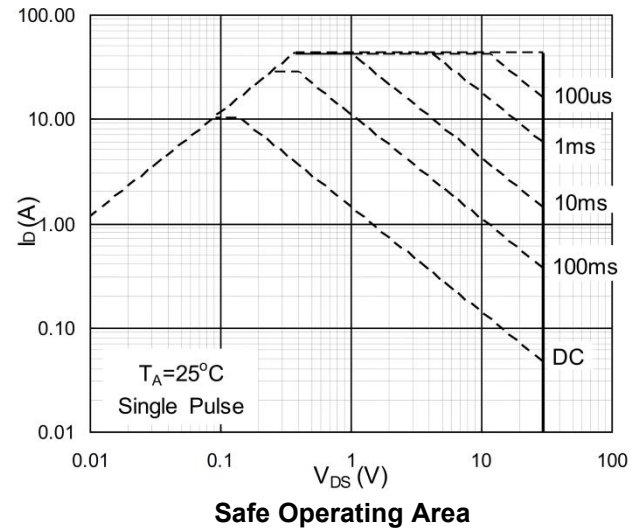
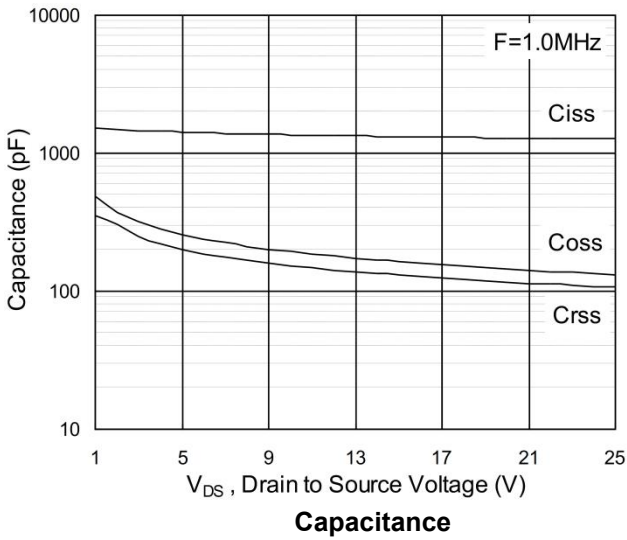
Gate-Charge Characteristics



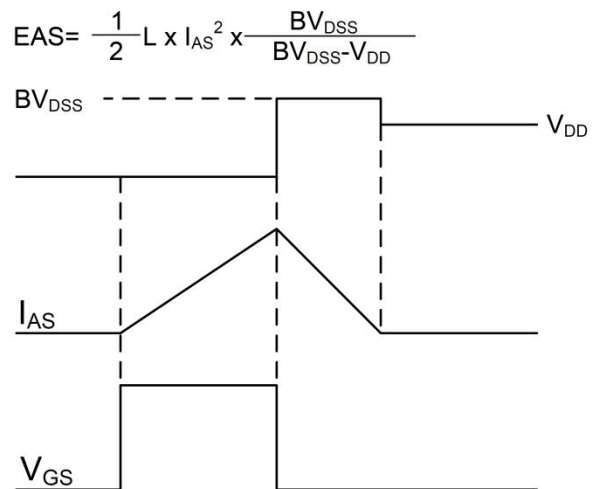
Normalized $V_{GS(th)}$ vs. T_J



Normalized $R_{DS(on)}$ vs. T_J



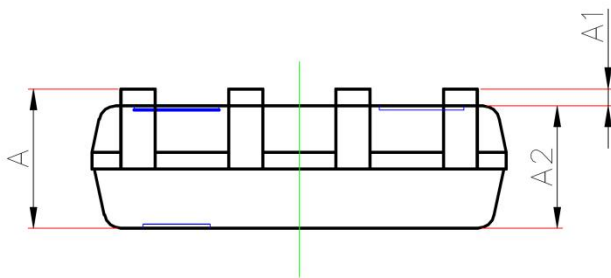
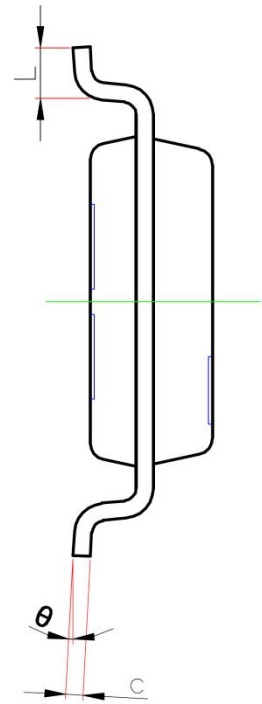
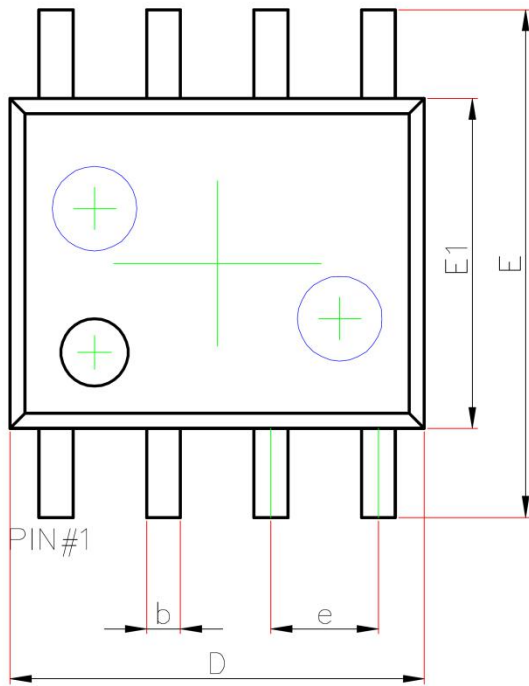
Switching Time Waveform



Unclamped Inductive Switching Waveform



SOP-8 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°